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### Understanding [Embedded - CPLDs \(Complex Programmable Logic Devices\)](#)

Embedded - CPLDs, or Complex Programmable Logic Devices, are highly versatile digital logic devices used in electronic systems. These programmable components are designed to perform complex logical operations and can be customized for specific applications. Unlike fixed-function ICs, CPLDs offer the flexibility to reprogram their configuration, making them an ideal choice for various embedded systems. They consist of a set of logic gates and programmable interconnects, allowing designers to implement complex logic circuits without needing custom hardware.

### Applications of Embedded - CPLDs

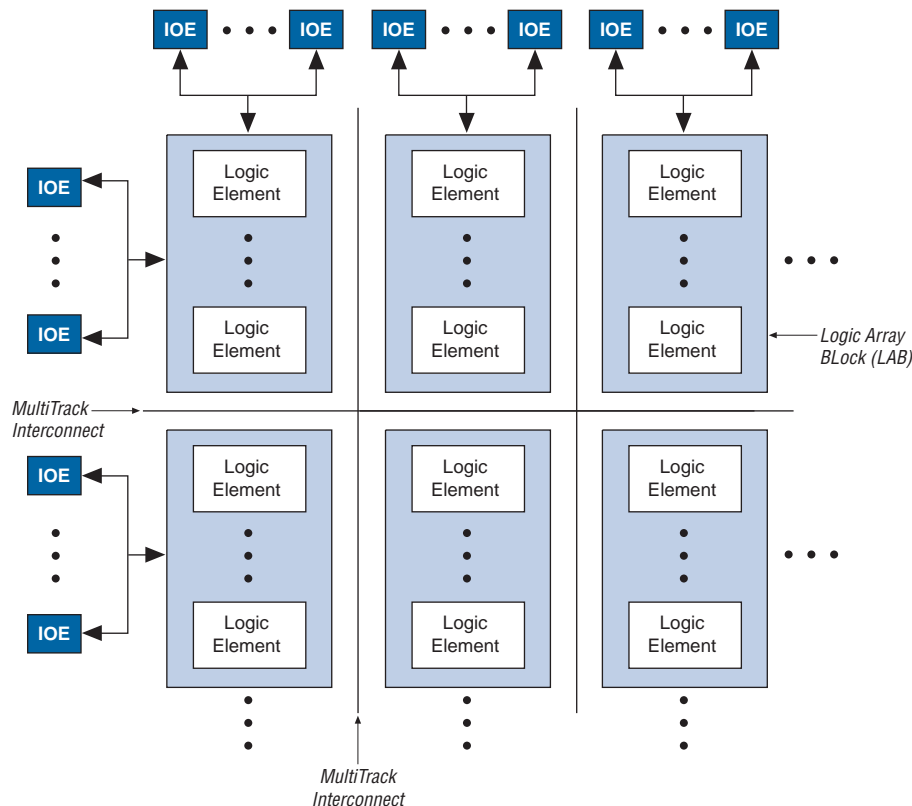
#### Details

Product Status	Active
Programmable Type	In System Programmable
Delay Time tpd(1) Max	5.4 ns
Voltage Supply - Internal	1.71V ~ 1.89V
Number of Logic Elements/Blocks	570
Number of Macrocells	440
Number of Gates	-
Number of I/O	160
Operating Temperature	0°C ~ 85°C (TJ)
Mounting Type	Surface Mount
Package / Case	256-BGA
Supplier Device Package	256-FBGA (17x17)
Purchase URL	<a href="https://www.e-xfl.com/product-detail/intel/epm570gf256c4n">https://www.e-xfl.com/product-detail/intel/epm570gf256c4n</a>




Figure 2–1 shows a functional block diagram of the MAX II device.

**Figure 2–1.** MAX II Device Block Diagram

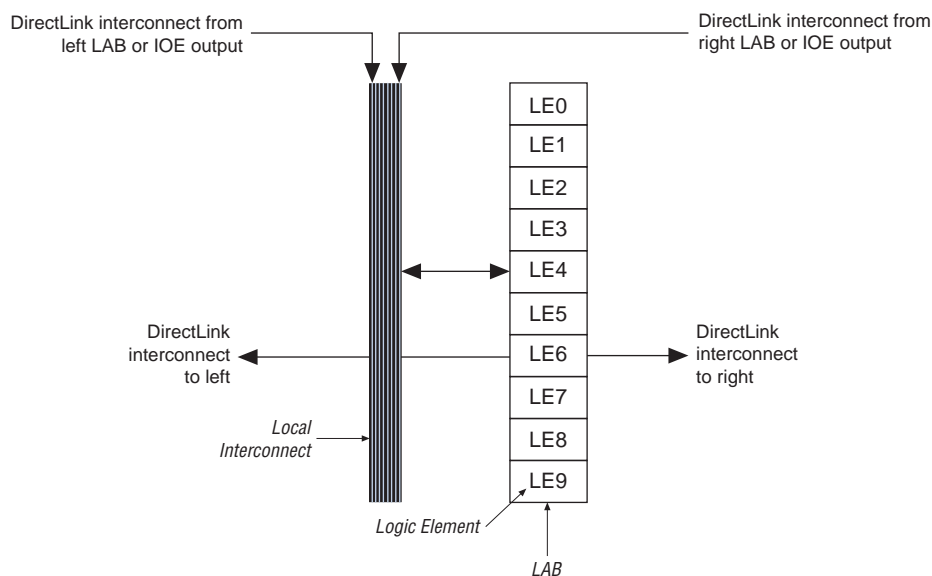


Each MAX II device contains a flash memory block within its floorplan. On the EPM240 device, this block is located on the left side of the device. On the EPM570, EPM1270, and EPM2210 devices, the flash memory block is located on the bottom-left area of the device. The majority of this flash memory storage is partitioned as the dedicated configuration flash memory (CFM) block. The CFM block provides the non-volatile storage for all of the SRAM configuration information. The CFM automatically downloads and configures the logic and I/O at power-up, providing instant-on operation.

 For more information about configuration upon power-up, refer to the *Hot Socketing and Power-On Reset in MAX II Devices* chapter in the MAX II Device Handbook.

A portion of the flash memory within the MAX II device is partitioned into a small block for user data. This user flash memory (UFM) block provides 8,192 bits of general-purpose user storage. The UFM provides programmable port connections to the logic array for reading and writing. There are three LAB rows adjacent to this block, with column numbers varying by device.

Table 2–1 shows the number of LAB rows and columns in each device, as well as the number of LAB rows and columns adjacent to the flash memory area in the EPM570, EPM1270, and EPM2210 devices. The long LAB rows are full LAB rows that extend from one side of row I/O blocks to the other. The short LAB rows are adjacent to the UFM block; their length is shown as width in LAB columns.

**Figure 2-4.** DirectLink Connection

## LAB Control Signals

Each LAB contains dedicated logic for driving control signals to its LEs. The control signals include two clocks, two clock enables, two asynchronous clears, a synchronous clear, an asynchronous preset/load, a synchronous load, and add/subtract control signals, providing a maximum of 10 control signals at a time. Although synchronous load and clear signals are generally used when implementing counters, they can also be used with other functions.

Each LAB can use two clocks and two clock enable signals. Each LAB's clock and clock enable signals are linked. For example, any LE in a particular LAB using the `labclk1` signal also uses `labckena1`. If the LAB uses both the rising and falling edges of a clock, it also uses both LAB-wide clock signals. Deasserting the clock enable signal turns off the LAB-wide clock.

Each LAB can use two asynchronous clear signals and an asynchronous load/preset signal. By default, the Quartus II software uses a NOT gate push-back technique to achieve preset. If you disable the NOT gate push-back option or assign a given register to power-up high using the Quartus II software, the preset is then achieved using the asynchronous load signal with asynchronous load data input tied high.

With the LAB-wide `addsub` control signal, a single LE can implement a one-bit adder and subtractor. This saves LE resources and improves performance for logic functions such as correlators and signed multipliers that alternate between addition and subtraction depending on data.

The LAB column clocks [3..0], driven by the global clock network, and LAB local interconnect generate the LAB-wide control signals. The MultiTrack interconnect structure drives the LAB local interconnect for non-global control signal generation. The MultiTrack interconnect's inherent low skew allows clock and control signal distribution in addition to data. [Figure 2-5](#) shows the LAB control signal generation circuit.

The Quartus II software automatically creates carry chain logic during design processing, or you can create it manually during design entry. Parameterized functions such as LPM functions automatically take advantage of carry chains for the appropriate functions. The Quartus II software creates carry chains longer than 10 LEs by linking adjacent LABs within the same row together automatically. A carry chain can extend horizontally up to one full LAB row, but does not extend between LAB rows.

### Clear and Preset Logic Control

LAB-wide signals control the logic for the register's clear and preset signals. The LE directly supports an asynchronous clear and preset function. The register preset is achieved through the asynchronous load of a logic high. MAX II devices support simultaneous preset/asynchronous load and clear signals. An asynchronous clear signal takes precedence if both signals are asserted simultaneously. Each LAB supports up to two clears and one preset signal.

In addition to the clear and preset ports, MAX II devices provide a chip-wide reset pin (`DEV_CLRn`) that resets all registers in the device. An option set before compilation in the Quartus II software controls this pin. This chip-wide reset overrides all other control signals and uses its own dedicated routing resources (that is, it does not use any of the four global resources). Driving this signal low before or during power-up prevents user mode from releasing clears within the design. This allows you to control when clear is released on a device that has just been powered-up. If not set for its chip-wide reset function, the `DEV_CLRn` pin is a regular I/O pin.

By default, all registers in MAX II devices are set to power-up low. However, this power-up state can be set to high on individual registers during design entry using the Quartus II software.

## MultiTrack Interconnect

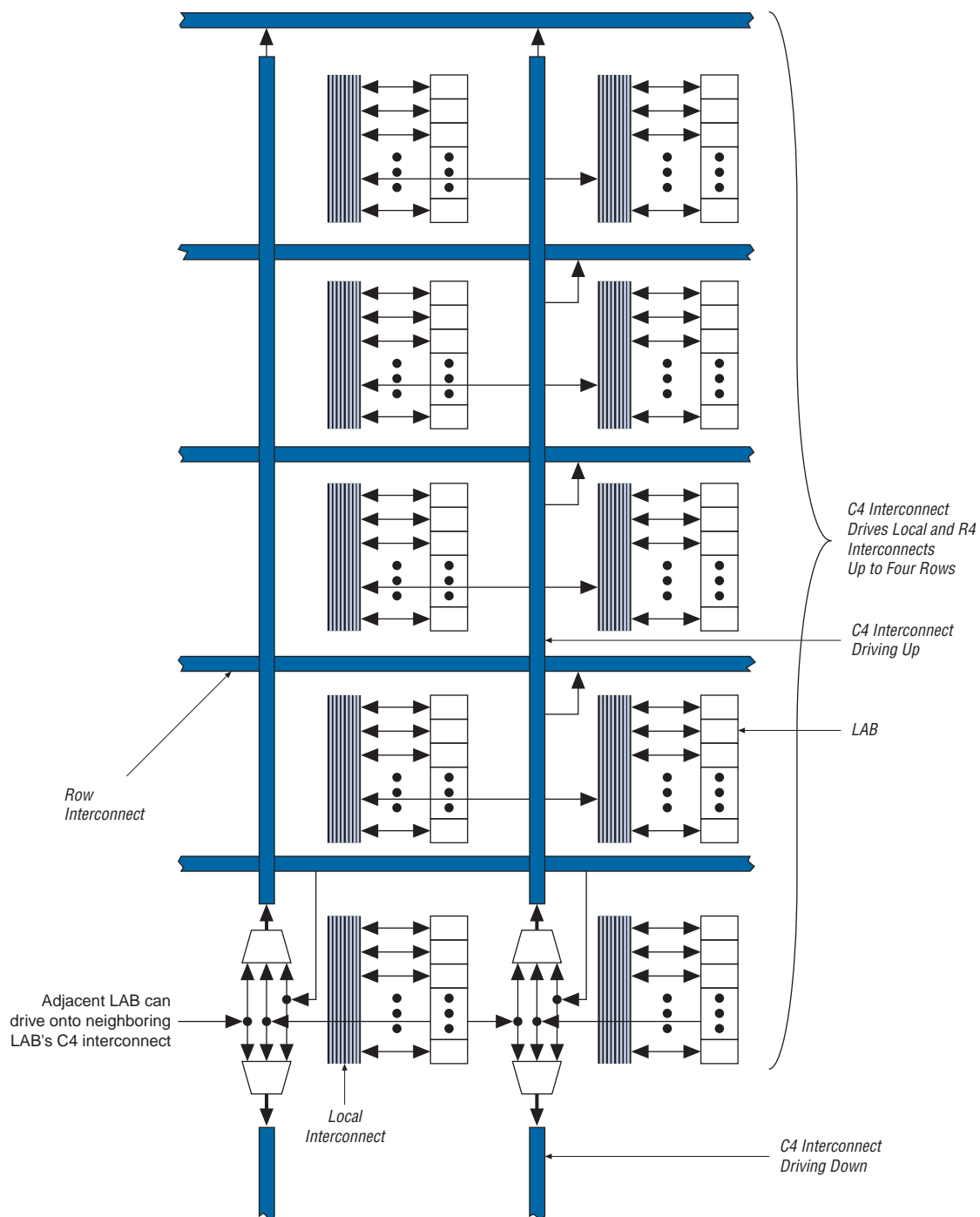
In the MAX II architecture, connections between LEs, the UFM, and device I/O pins are provided by the MultiTrack interconnect structure. The MultiTrack interconnect consists of continuous, performance-optimized routing lines used for inter- and intra-design block connectivity. The Quartus II Compiler automatically places critical design paths on faster interconnects to improve design performance.

The MultiTrack interconnect consists of row and column interconnects that span fixed distances. A routing structure with fixed length resources for all devices allows predictable and short delays between logic levels instead of large delays associated with global or long routing lines. Dedicated row interconnects route signals to and from LABs within the same row. These row resources include:

- DirectLink interconnects between LABs
- R4 interconnects traversing four LABs to the right or left

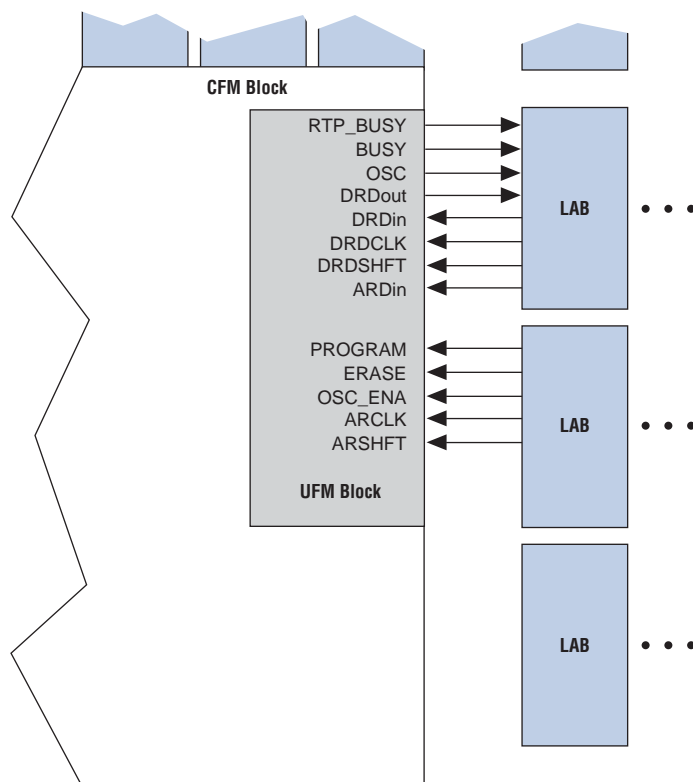
The DirectLink interconnect allows an LAB to drive into the local interconnect of its left and right neighbors. The DirectLink interconnect provides fast communication between adjacent LABs and/or blocks without using row interconnect resources.

**Figure 2-12.** C4 Interconnect Connections *(Note 1)*



**Note to Figure 2-12:**

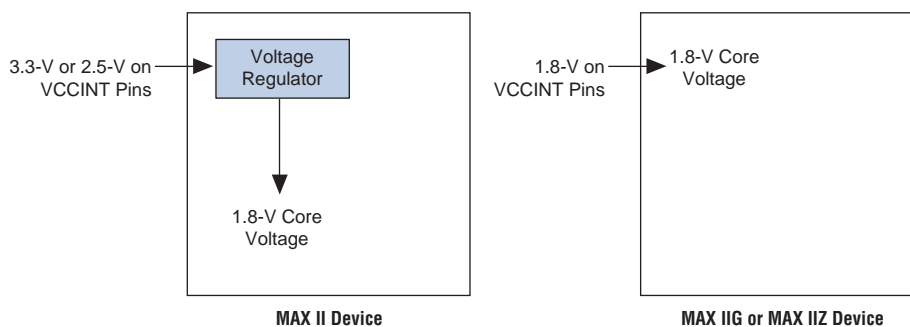
(1) Each C4 interconnect can drive either up or down four rows.

**Figure 2-17.** EPM570, EPM1270, and EPM2210 UFM Block LAB Row Interface

## MultiVolt Core

The MAX II architecture supports the MultiVolt core feature, which allows MAX II devices to support multiple  $V_{CC}$  levels on the  $V_{CCINT}$  supply. An internal linear voltage regulator provides the necessary 1.8-V internal voltage supply to the device. The voltage regulator supports 3.3-V or 2.5-V supplies on its inputs to supply the 1.8-V internal voltage to the device, as shown in Figure 2-18. The voltage regulator is not guaranteed for voltages that are between the maximum recommended 2.5-V operating voltage and the minimum recommended 3.3-V operating voltage.

The MAX IIG and MAX IIZ devices use external 1.8-V supply. The 1.8-V  $V_{CC}$  external supply powers the device core directly.

**Figure 2-18.** MultiVolt Core Feature in MAX II Devices

## I/O Structure

IOEs support many features, including:

- LVTTTL and LVCMOS I/O standards
- 3.3-V, 32-bit, 66-MHz PCI compliance
- Joint Test Action Group (JTAG) boundary-scan test (BST) support
- Programmable drive strength control
- Weak pull-up resistors during power-up and in system programming
- Slew-rate control
- Tri-state buffers with individual output enable control
- Bus-hold circuitry
- Programmable pull-up resistors in user mode
- Unique output enable per pin
- Open-drain outputs
- Schmitt trigger inputs
- Fast I/O connection
- Programmable input delay

MAX II device IOEs contain a bidirectional I/O buffer. [Figure 2-19](#) shows the MAX II IOE structure. Registers from adjacent LABs can drive to or be driven from the IOE's bidirectional I/O buffers. The Quartus II software automatically attempts to place registers in the adjacent LAB with fast I/O connection to achieve the fastest possible clock-to-output and registered output enable timing. For input registers, the Quartus II software automatically routes the register to guarantee zero hold time. You can set timing assignments in the Quartus II software to achieve desired I/O timing.

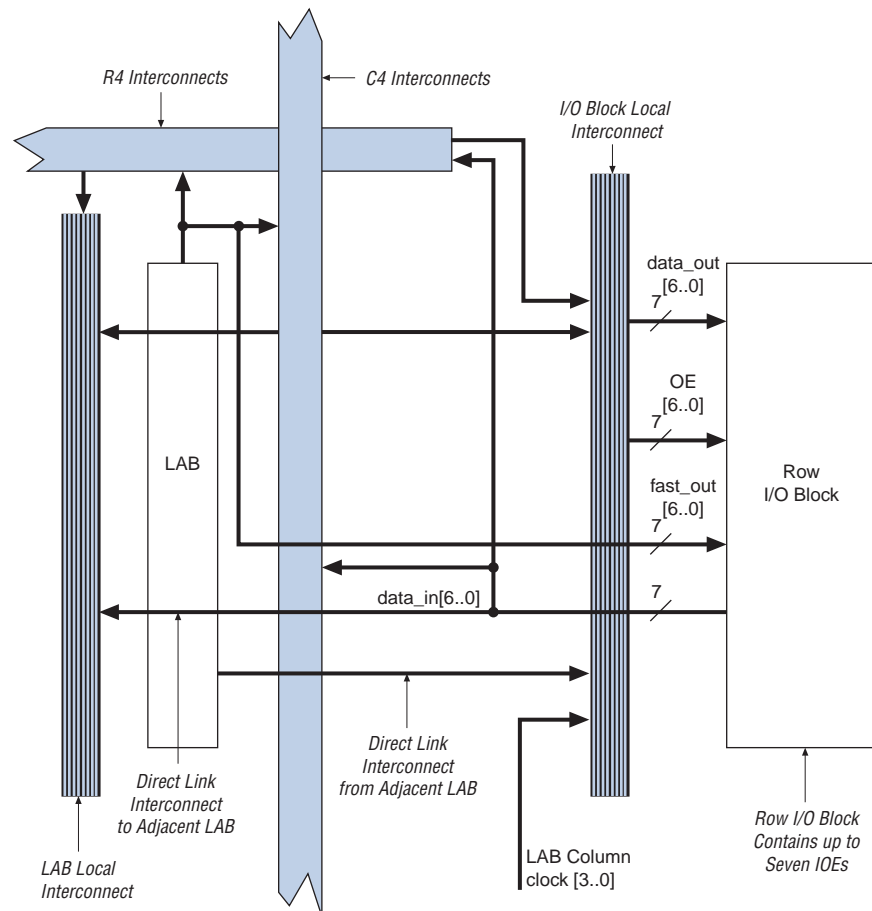
### Fast I/O Connection

A dedicated fast I/O connection from the adjacent LAB to the IOEs within an I/O block provides faster output delays for clock-to-output and  $t_{PD}$  propagation delays. This connection exists for data output signals, not output enable signals or input signals. [Figure 2-20](#), [Figure 2-21](#), and [Figure 2-22](#) illustrate the fast I/O connection.



Figure 2-20 shows how a row I/O block connects to the logic array.

**Figure 2-20.** Row I/O Block Connection to the Interconnect (Note 1)



**Note to Figure 2-20:**

- (1) Each of the seven IOEs in the row I/O block can have one data\_out or fast\_out output, one OE output, and one data\_in input.

**Table 2-6.** Programmable Drive Strength *(Note 1)*

I/O Standard	IOH/IOL Current Strength Setting (mA)
3.3-V LVTTTL	16
	8
3.3-V LVCMOS	8
	4
2.5-V LVTTTL/LVCMOS	14
	7
1.8-V LVTTTL/LVCMOS	6
	3
1.5-V LVCMOS	4
	2

**Note to Table 2-6:**

- (1) The  $I_{OH}$  current strength numbers shown are for a condition of a  $V_{OUT} = V_{OH}$  minimum, where the  $V_{OH}$  minimum is specified by the I/O standard. The  $I_{OL}$  current strength numbers shown are for a condition of a  $V_{OUT} = V_{OL}$  maximum, where the  $V_{OL}$  maximum is specified by the I/O standard. For 2.5-V LVTTTL/LVCMOS, the  $I_{OH}$  condition is  $V_{OUT} = 1.7$  V and the  $I_{OL}$  condition is  $V_{OUT} = 0.7$  V.

## Slew-Rate Control

The output buffer for each MAX II device I/O pin has a programmable output slew-rate control that can be configured for low noise or high-speed performance. A faster slew rate provides high-speed transitions for high-performance systems. However, these fast transitions may introduce noise transients into the system. A slow slew rate reduces system noise, but adds a nominal output delay to rising and falling edges. The lower the voltage standard (for example, 1.8-V LVTTTL) the larger the output delay when slow slew is enabled. Each I/O pin has an individual slew-rate control, allowing the designer to specify the slew rate on a pin-by-pin basis. The slew-rate control affects both the rising and falling edges.

## Open-Drain Output

MAX II devices provide an optional open-drain (equivalent to open-collector) output for each I/O pin. This open-drain output enables the device to provide system-level control signals (for example, interrupt and write enable signals) that can be asserted by any of several devices. This output can also provide an additional wired-OR plane.

## Programmable Ground Pins

Each unused I/O pin on MAX II devices can be used as an additional ground pin. This programmable ground feature does not require the use of the associated LEs in the device. In the Quartus II software, unused pins can be set as programmable GND on a global default basis or they can be individually assigned. Unused pins also have the option of being set as tri-stated input pins.


## Document Revision History

Table 2-8 shows the revision history for this chapter.

**Table 2-8.** Document Revision History

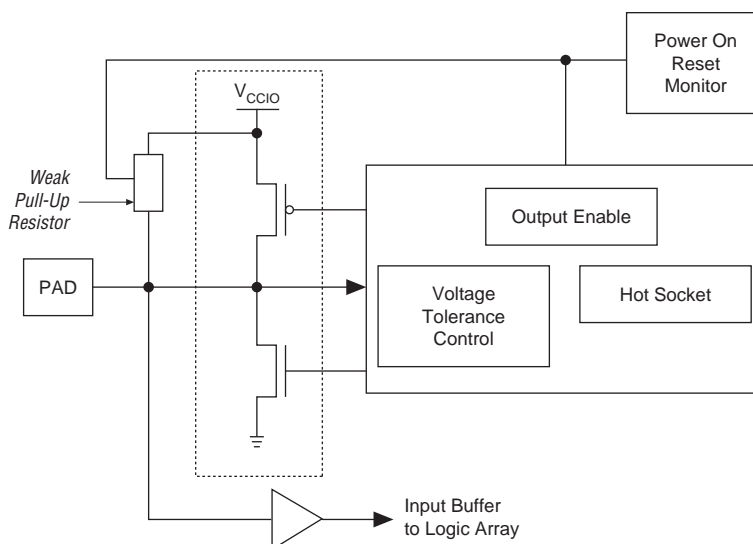
Date and Revision	Changes Made	Summary of Changes
October 2008, version 2.2	<ul style="list-style-type: none"> <li>■ Updated Table 2-4 and Table 2-6.</li> <li>■ Updated “I/O Standards and Banks” section.</li> <li>■ Updated New Document Format.</li> </ul>	—
March 2008, version 2.1	<ul style="list-style-type: none"> <li>■ Updated “Schmitt Trigger” section.</li> </ul>	—
December 2007, version 2.0	<ul style="list-style-type: none"> <li>■ Updated “Clear and Preset Logic Control” section.</li> <li>■ Updated “MultiVolt Core” section.</li> <li>■ Updated “MultiVolt I/O Interface” section.</li> <li>■ Updated Table 2-7.</li> <li>■ Added “Referenced Documents” section.</li> </ul>	Updated document with MAX IIZ information.
December 2006, version 1.7	<ul style="list-style-type: none"> <li>■ Minor update in “Internal Oscillator” section. Added document revision history.</li> </ul>	—
August 2006, version 1.6	<ul style="list-style-type: none"> <li>■ Updated functional description and I/O structure sections.</li> </ul>	—
July 2006, version 1.5	<ul style="list-style-type: none"> <li>■ Minor content and table updates.</li> </ul>	—
February 2006, version 1.4	<ul style="list-style-type: none"> <li>■ Updated “LAB Control Signals” section.</li> <li>■ Updated “Clear and Preset Logic Control” section.</li> <li>■ Updated “Internal Oscillator” section.</li> <li>■ Updated Table 2-5.</li> </ul>	—
August 2005, version 1.3	<ul style="list-style-type: none"> <li>■ Removed Note 2 from Table 2-7.</li> </ul>	—
December 2004, version 1.2	<ul style="list-style-type: none"> <li>■ Added a paragraph to page 2-15.</li> </ul>	—
June 2004, version 1.1	<ul style="list-style-type: none"> <li>■ Added CFM acronym. Corrected Figure 2-19.</li> </ul>	—




 Make sure that the  $V_{CCINT}$  is within the recommended operating range even though SRAM download has completed.

Each I/O and clock pin has the circuitry shown in [Figure 4-1](#).

**Figure 4-1.** Hot Socketing Circuit Block Diagram for MAX II Devices



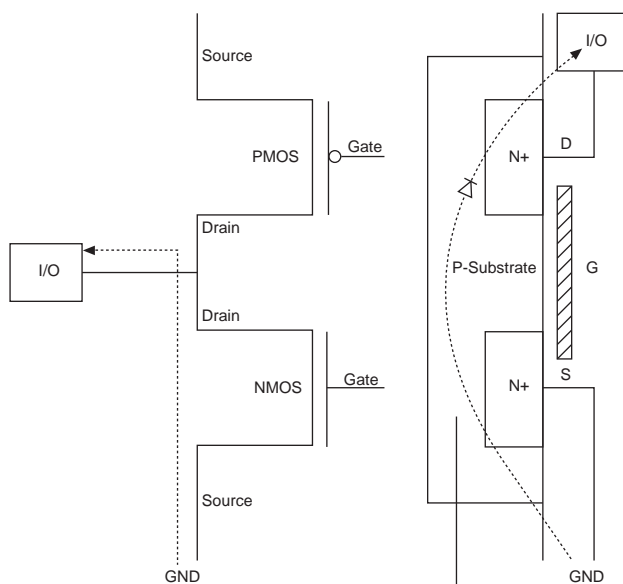
The POR circuit monitors  $V_{CCINT}$  and  $V_{CCIO}$  voltage levels and keeps I/O pins tri-stated until the device has completed its flash memory configuration of the SRAM logic. The weak pull-up resistor (R) from the I/O pin to  $V_{CCIO}$  is enabled during download to keep the I/O pins from floating. The 3.3-V tolerance control circuit permits the I/O pins to be driven by 3.3 V before  $V_{CCIO}$  and/or  $V_{CCINT}$  are powered, and it prevents the I/O pins from driving out when the device is not fully powered or operational. The hot socket circuit prevents I/O pins from internally powering  $V_{CCIO}$  and  $V_{CCINT}$  when driven by external signals before the device is powered.

 For information about 5.0-V tolerance, refer to the [Using MAX II Devices in Multi-Voltage Systems](#) chapter in the *MAX II Device Handbook*.

[Figure 4-2](#) shows a transistor-level cross section of the MAX II device I/O buffers. This design ensures that the output buffers do not drive when  $V_{CCIO}$  is powered before  $V_{CCINT}$  or if the I/O pad voltage is higher than  $V_{CCIO}$ . This also applies for sudden voltage spikes during hot insertion. The  $V_{PAD}$  leakage current charges the 3.3-V tolerant circuit capacitance.

When the I/O pin receives a negative ESD zap at the pin that is less than  $-0.7\text{ V}$  ( $0.7\text{ V}$  is the voltage drop across a diode), the intrinsic P-Substrate/N+ drain diode is forward biased. Therefore, the discharge ESD current path is from GND to the I/O pin, as shown in Figure 4-4.

**Figure 4-4.** ESD Protection During Negative Voltage Zap



## Power-On Reset Circuitry

MAX II devices have POR circuits to monitor  $V_{CCINT}$  and  $V_{CCIO}$  voltage levels during power-up. The POR circuit monitors these voltages, triggering download from the non-volatile configuration flash memory (CFM) block to the SRAM logic, maintaining tri-state of the I/O pins (with weak pull-up resistors enabled) before and during this process. When the MAX II device enters user mode, the POR circuit releases the I/O pins to user functionality. The POR circuit of the MAX II (except MAX IIZ) device continues to monitor the  $V_{CCINT}$  voltage level to detect a brown-out condition. The POR circuit of the MAX IIZ device does not monitor the  $V_{CCINT}$  voltage level after the device enters into user mode. More details are provided in the following sub-sections.

## Recommended Operating Conditions

Table 5-2 shows the MAX II device family recommended operating conditions.

**Table 5-2.** MAX II Device Recommended Operating Conditions

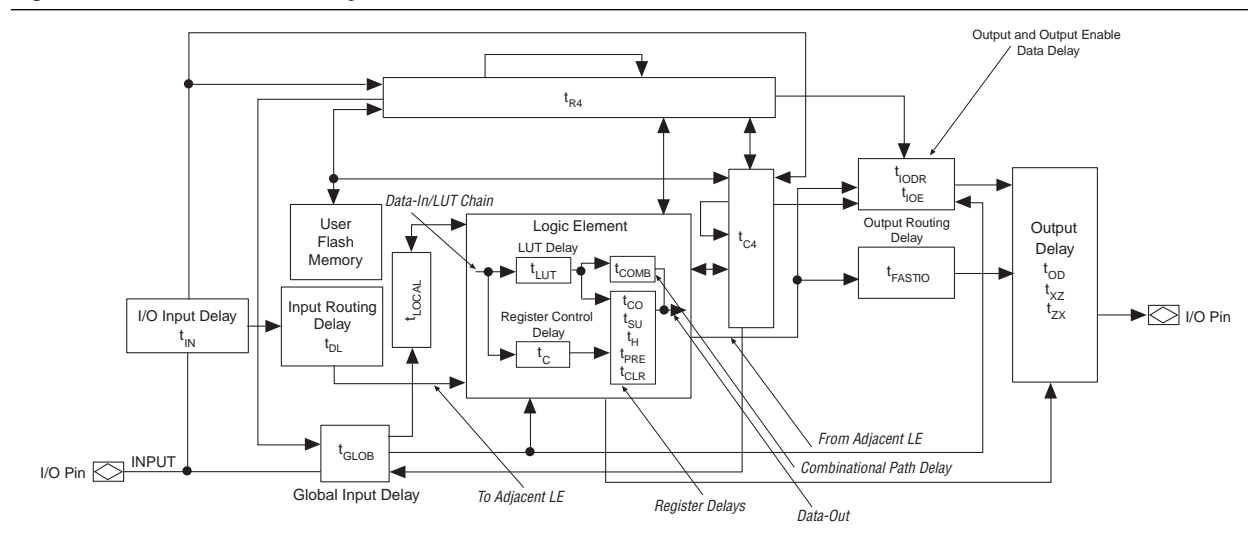
Symbol	Parameter	Conditions	Minimum	Maximum	Unit
$V_{CCINT}$ (1)	3.3-V supply voltage for internal logic and ISP	MAX II devices	3.00	3.60	V
	2.5-V supply voltage for internal logic and ISP	MAX II devices	2.375	2.625	V
	1.8-V supply voltage for internal logic and ISP	MAX IIG and MAX IIZ devices	1.71	1.89	V
$V_{CCIO}$ (1)	Supply voltage for I/O buffers, 3.3-V operation	—	3.00	3.60	V
	Supply voltage for I/O buffers, 2.5-V operation	—	2.375	2.625	V
	Supply voltage for I/O buffers, 1.8-V operation	—	1.71	1.89	V
	Supply voltage for I/O buffers, 1.5-V operation	—	1.425	1.575	V
$V_I$	Input voltage	(2), (3), (4)	–0.5	4.0	V
$V_O$	Output voltage	—	0	$V_{CCIO}$	V
$T_J$	Operating junction temperature	Commercial range	0	85	°C
		Industrial range	–40	100	°C
		Extended range (5)	–40	125	°C

**Notes to Table 5-2:**

- (1) MAX II device in-system programming and/or user flash memory (UFM) programming via JTAG or logic array is not guaranteed outside the recommended operating conditions (for example, if brown-out occurs in the system during a potential write/program sequence to the UFM, users are recommended to read back UFM contents and verify against the intended write data).
- (2) Minimum DC input is –0.5 V. During transitions, the inputs may undershoot to –2.0 V for input currents less than 100 mA and periods shorter than 20 ns.
- (3) During transitions, the inputs may overshoot to the voltages shown in the following table based upon input duty cycle. The DC case is equivalent to 100% duty cycle. For more information about 5.0-V tolerance, refer to the *Using MAX II Devices in Multi-Voltage Systems* chapter in the *MAX II Device Handbook*.

$V_{IN}$	Max. Duty Cycle
4.0 V	100% (DC)
4.1	90%
4.2	50%
4.3	30%
4.4	17%
4.5	10%
- (4) All pins, including clock, I/O, and JTAG pins, may be driven before  $V_{CCINT}$  and  $V_{CCIO}$  are powered.
- (5) For the extended temperature range of 100 to 125° C, MAX II UFM programming (erase/write) is only supported via the JTAG interface. UFM programming via the logic array interface is not guaranteed in this range.

**Figure 5-2.** MAX II Device Timing Model



The timing characteristics of any signal path can be derived from the timing model and parameters of a particular device. External timing parameters, which represent pin-to-pin timing delays, can be calculated as the sum of internal parameters.



Refer to the *Understanding Timing in MAX II Devices* chapter in the *MAX II Device Handbook* for more information.

This section describes and specifies the performance, internal, external, and UFM timing specifications. All specifications are representative of the worst-case supply voltage and junction temperature conditions.

## Preliminary and Final Timing

Timing models can have either preliminary or final status. The Quartus II software issues an informational message during the design compilation if the timing models are preliminary. Table 5-13 shows the status of the MAX II device timing models.

Preliminary status means the timing model is subject to change. Initially, timing numbers are created using simulation results, process data, and other known parameters. These tests are used to make the preliminary numbers as close to the actual timing parameters as possible.

Final timing numbers are based on actual device operation and testing. These numbers reflect the actual performance of the device under the worst-case voltage and junction temperature conditions.

**Table 5-13.** MAX II Device Timing Model Status (Part 1 of 2)

Device	Preliminary	Final
EPM240	—	✓
EPM240Z (1)	—	✓
EPM570	—	✓
EPM570Z (1)	—	✓



## Internal Timing Parameters

Internal timing parameters are specified on a speed grade basis independent of device density. Table 5-15 through Table 5-22 describe the MAX II device internal timing microparameters for logic elements (LEs), input/output elements (IOEs), UFM blocks, and MultiTrack interconnects. The timing values for -3, -4, and -5 speed grades shown in Table 5-15 through Table 5-22 are based on an EPM1270 device target, while -6, -7, and -8 speed grade values are based on an EPM570Z device target.



For more explanations and descriptions about each internal timing microparameters symbol, refer to the *Understanding Timing in MAX II Devices* chapter in the *MAX II Device Handbook*.

**Table 5-15.** LE Internal Timing Microparameters

Symbol	Parameter	MAX II / MAX IIG						MAX IIZ						Unit
		-3 Speed Grade		-4 Speed Grade		-5 Speed Grade		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
t <sub>LUT</sub>	LE combinational LUT delay	—	571	—	742	—	914	—	1,215	—	2,247	—	2,247	ps
t <sub>COMB</sub>	Combinational path delay	—	147	—	192	—	236	—	243	—	305	—	309	ps
t <sub>CLR</sub>	LE register clear delay	238	—	309	—	381	—	401	—	541	—	545	—	ps
t <sub>PRE</sub>	LE register preset delay	238	—	309	—	381	—	401	—	541	—	545	—	ps
t <sub>SU</sub>	LE register setup time before clock	208	—	271	—	333	—	260	—	319	—	321	—	ps
t <sub>H</sub>	LE register hold time after clock	0	—	0	—	0	—	0	—	0	—	0	—	ps
t <sub>CO</sub>	LE register clock-to-output delay	—	235	—	305	—	376	—	380	—	489	—	494	ps
t <sub>CLKHL</sub>	Minimum clock high or low time	166	—	216	—	266	—	253	—	335	—	339	—	ps
t <sub>C</sub>	Register control delay	—	857	—	1,114	—	1,372	—	1,356	—	1,722	—	1,741	ps

## External Timing Parameters

External timing parameters are specified by device density and speed grade. All external I/O timing parameters shown are for the 3.3-V LVTTTL I/O standard with the maximum drive strength and fast slew rate. For external I/O timing using standards other than LVTTTL or for different drive strengths, use the I/O standard input and output delay adders in [Table 5-27](#) through [Table 5-31](#).



For more information about each external timing parameters symbol, refer to the [Understanding Timing in MAX II Devices](#) chapter in the *MAX II Device Handbook*.

[Table 5-23](#) shows the external I/O timing parameters for EPM240 devices.

**Table 5-23.** EPM240 Global Clock External I/O Timing Parameters (Part 1 of 2)

Symbol	Parameter	Condition	MAX II / MAX IIG						MAX IIZ						Unit
			-3 Speed Grade		-4 Speed Grade		-5 Speed Grade		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
t <sub>PD1</sub>	Worst case pin-to-pin delay through 1 look-up table (LUT)	10 pF	—	4.7	—	6.1	—	7.5	—	7.9	—	12.0	—	14.0	ns
t <sub>PD2</sub>	Best case pin-to-pin delay through 1 LUT	10 pF	—	3.7	—	4.8	—	5.9	—	5.8	—	7.8	—	8.5	ns
t <sub>SU</sub>	Global clock setup time	—	1.7	—	2.2	—	2.7	—	2.4	—	4.1	—	4.6	—	ns
t <sub>H</sub>	Global clock hold time	—	0	—	0	—	0	—	0	—	0	—	0	—	ns
t <sub>CO</sub>	Global clock to output delay	10 pF	2.0	4.3	2.0	5.6	2.0	6.9	2.0	6.6	2.0	8.1	2.0	8.6	ns
t <sub>CH</sub>	Global clock high time	—	166	—	216	—	266	—	253	—	335	—	339	—	ps
t <sub>CL</sub>	Global clock low time	—	166	—	216	—	266	—	253	—	335	—	339	—	ps
t <sub>CNT</sub>	Minimum global clock period for 16-bit counter	—	3.3	—	4.0	—	5.0	—	5.4	—	8.1	—	8.4	—	ns

**Table 5-24.** EPM570 Global Clock External I/O Timing Parameters (Part 2 of 2)

Symbol	Parameter	Condition	MAX II / MAX IIG						MAX IIZ						Unit
			−3 Speed Grade		−4 Speed Grade		−5 Speed Grade		−6 Speed Grade		−7 Speed Grade		−8 Speed Grade		
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
f <sub>CNT</sub>	Maximum global clock frequency for 16-bit counter	—	—	304.0 (1)	—	247.5	—	201.1	—	184.1	—	123.5	—	118.3	MHz

**Note to Table 5-24:**

- (1) The maximum frequency is limited by the I/O standard on the clock input pin. The 16-bit counter critical delay performs faster than this global clock input pin maximum frequency.

Table 5-25 shows the external I/O timing parameters for EPM1270 devices.

**Table 5-25.** EPM1270 Global Clock External I/O Timing Parameters

Symbol	Parameter	Condition	MAX II / MAX IIG						Unit
			–3 Speed Grade		–4 Speed Grade		–5 Speed Grade		
			Min	Max	Min	Max	Min	Max	
t <sub>PD1</sub>	Worst case pin-to-pin delay through 1 look-up table (LUT)	10 pF	—	6.2	—	8.1	—	10.0	ns
t <sub>PD2</sub>	Best case pin-to-pin delay through 1 LUT	10 pF	—	3.7	—	4.8	—	5.9	ns
t <sub>SU</sub>	Global clock setup time	—	1.2	—	1.5	—	1.9	—	ns
t <sub>H</sub>	Global clock hold time	—	0	—	0	—	0	—	ns
t <sub>CO</sub>	Global clock to output delay	10 pF	2.0	4.6	2.0	5.9	2.0	7.3	ns
t <sub>CH</sub>	Global clock high time	—	166	—	216	—	266	—	ps
t <sub>CL</sub>	Global clock low time	—	166	—	216	—	266	—	ps
t <sub>CNT</sub>	Minimum global clock period for 16-bit counter	—	3.3	—	4.0	—	5.0	—	ns
f <sub>CNT</sub>	Maximum global clock frequency for 16-bit counter	—	—	304.0 (1)	—	247.5	—	201.1	MHz

**Note to Table 5-25:**

- (1) The maximum frequency is limited by the I/O standard on the clock input pin. The 16-bit counter critical delay performs faster than this global clock input pin maximum frequency.

Table 5–26 shows the external I/O timing parameters for EPM2210 devices.

**Table 5–26.** EPM2210 Global Clock External I/O Timing Parameters

Symbol	Parameter	Condition	MAX II / MAX IIG						Unit
			–3 Speed Grade		–4 Speed Grade		–5 Speed Grade		
			Min	Max	Min	Max	Min	Max	
t <sub>PD1</sub>	Worst case pin-to-pin delay through 1 look-up table (LUT)	10 pF	—	7.0	—	9.1	—	11.2	ns
t <sub>PD2</sub>	Best case pin-to-pin delay through 1 LUT	10 pF	—	3.7	—	4.8	—	5.9	ns
t <sub>SU</sub>	Global clock setup time	—	1.2	—	1.5	—	1.9	—	ns
t <sub>H</sub>	Global clock hold time	—	0	—	0	—	0	—	ns
t <sub>CO</sub>	Global clock to output delay	10 pF	2.0	4.6	2.0	6.0	2.0	7.4	ns
t <sub>CH</sub>	Global clock high time	—	166	—	216	—	266	—	ps
t <sub>CL</sub>	Global clock low time	—	166	—	216	—	266	—	ps
t <sub>CNT</sub>	Minimum global clock period for 16-bit counter	—	3.3	—	4.0	—	5.0	—	ns
f <sub>CNT</sub>	Maximum global clock frequency for 16-bit counter	—	—	304.0 (1)	—	247.5	—	201.1	MHz

**Note to Table 5–26:**

- (1) The maximum frequency is limited by the I/O standard on the clock input pin. The 16-bit counter critical delay performs faster than this global clock input pin maximum frequency.

## External Timing I/O Delay Adders

The I/O delay timing parameters for I/O standard input and output adders, and input delays are specified by speed grade independent of device density.

Table 5–27 through Table 5–31 show the adder delays associated with I/O pins for all packages. The delay numbers for –3, –4, and –5 speed grades shown in Table 5–27 through Table 5–33 are based on an EPM1270 device target, while –6, –7, and –8 speed grade values are based on an EPM570Z device target. If an I/O standard other than 3.3-V LVTTTL is selected, add the input delay adder to the external  $t_{SU}$  timing parameters shown in Table 5–23 through Table 5–26. If an I/O standard other than 3.3-V LVTTTL with 16 mA drive strength and fast slew rate is selected, add the output delay adder to the external  $t_{CO}$  and  $t_{PD}$  shown in Table 5–23 through Table 5–26.

**Table 5–27.** External Timing Input Delay Adders (Part 1 of 2)

I/O Standard		MAX II / MAX IIG						MAX IIZ						Unit
		–3 Speed Grade		–4 Speed Grade		–5 Speed Grade		–6 Speed Grade		–7 Speed Grade		–8 Speed Grade		
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
3.3-V LVTTTL	Without Schmitt Trigger	—	0	—	0	—	0	—	0	—	0	—	0	ps
	With Schmitt Trigger	—	334	—	434	—	535	—	387	—	434	—	442	ps

**Table 5-29.** External Timing Output Delay and  $t_{OD}$  Adders for Fast Slew Rate

I/O Standard		MAX II / MAX IIG						MAX IIZ						Unit
		-3 Speed Grade		-4 Speed Grade		-5 Speed Grade		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
3.3-V LVTTTL	16 mA	—	0	—	0	—	0	—	0	—	0	—	0	ps
	8 mA	—	65	—	84	—	104	—	-6	—	-2	—	-3	ps
3.3-V LVCMOS	8 mA	—	0	—	0	—	0	—	0	—	0	—	0	ps
	4 mA	—	65	—	84	—	104	—	-6	—	-2	—	-3	ps
2.5-V LVTTTL / LVCMOS	14 mA	—	122	—	158	—	195	—	-63	—	-71	—	-88	ps
	7 mA	—	193	—	251	—	309	—	10	—	-1	—	1	ps
1.8-V LVTTTL / LVCMOS	6 mA	—	568	—	738	—	909	—	128	—	118	—	118	ps
	3 mA	—	654	—	850	—	1,046	—	352	—	327	—	332	ps
1.5-V LVCMOS	4 mA	—	1,059	—	1,376	—	1,694	—	421	—	400	—	400	ps
	2 mA	—	1,167	—	1,517	—	1,867	—	757	—	743	—	743	ps
3.3-V PCI	20 mA	—	3	—	4	—	5	—	-6	—	-2	—	-3	ps

**Table 5-30.** External Timing Output Delay and  $t_{OD}$  Adders for Slow Slew Rate

I/O Standard		MAX II / MAX IIG						MAX IIZ						Unit
		-3 Speed Grade		-4 Speed Grade		-5 Speed Grade		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
3.3-V LVTTTL	16 mA	—	7,064	—	6,745	—	6,426	—	5,966	—	5,992	—	6,118	ps
	8 mA	—	7,946	—	7,627	—	7,308	—	6,541	—	6,570	—	6,720	ps
3.3-V LVCMOS	8 mA	—	7,064	—	6,745	—	6,426	—	5,966	—	5,992	—	6,118	ps
	4 mA	—	7,946	—	7,627	—	7,308	—	6,541	—	6,570	—	6,720	ps
2.5-V LVTTTL / LVCMOS	14 mA	—	10,434	—	10,115	—	9,796	—	9,141	—	9,154	—	9,297	ps
	7 mA	—	11,548	—	11,229	—	10,910	—	9,861	—	9,874	—	10,037	ps
1.8-V LVTTTL / LVCMOS	6 mA	—	22,927	—	22,608	—	22,289	—	21,811	—	21,854	—	21,857	ps
	3 mA	—	24,731	—	24,412	—	24,093	—	23,081	—	23,034	—	23,107	ps
1.5-V LVCMOS	4 mA	—	38,723	—	38,404	—	38,085	—	39,121	—	39,124	—	39,124	ps
	2 mA	—	41,330	—	41,011	—	40,692	—	40,631	—	40,634	—	40,634	ps
3.3-V PCI	20 mA	—	261	—	339	—	418	—	6,644	—	6,627	—	6,914	ps